

## **ABSTRACT OF THE DISCLOSURE**

### **BACKSIDE BURIED STRAP FOR SOI DRAM TRENCH CAPACITOR**

1     In SOI integrated circuits having trench capacitor DRAM arrays, the  
2     decreasing thickness of the insulating layer causes cross-talk between the  
3     passing wordline traveling over the trench capacitor. Increasing the depth  
4     of the recess at the top of the trench and undercutting the insulating layer  
5     laterally permits the buried strap from the capacitor center electrode to make  
6     contact to the back side of the SOI layer, thereby increasing the vertical  
7     separation between the passing wordline and the strap.